

1/6

FIG 1A

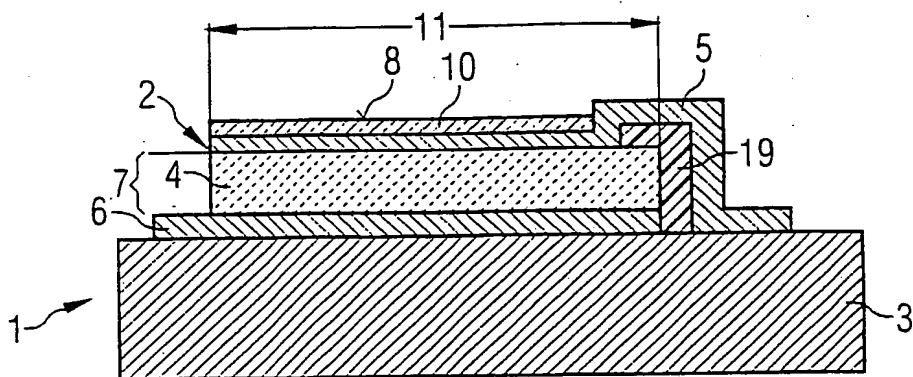


FIG 1B

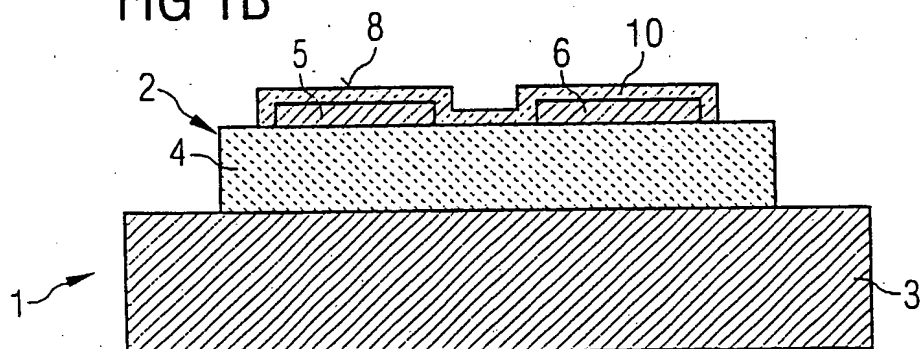
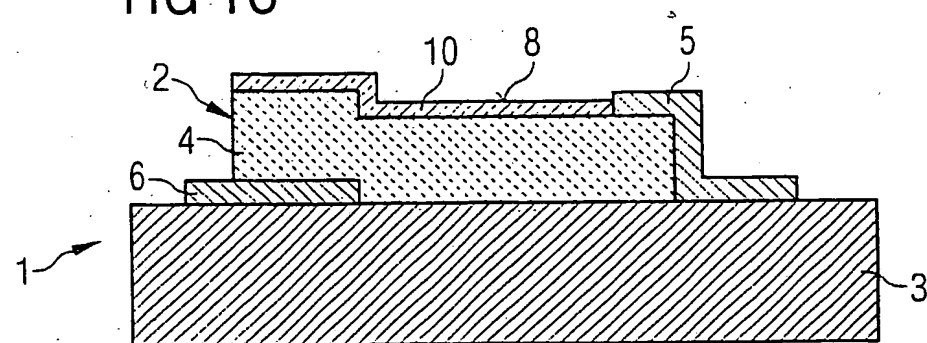


FIG 1C



2/6

FIG 1D

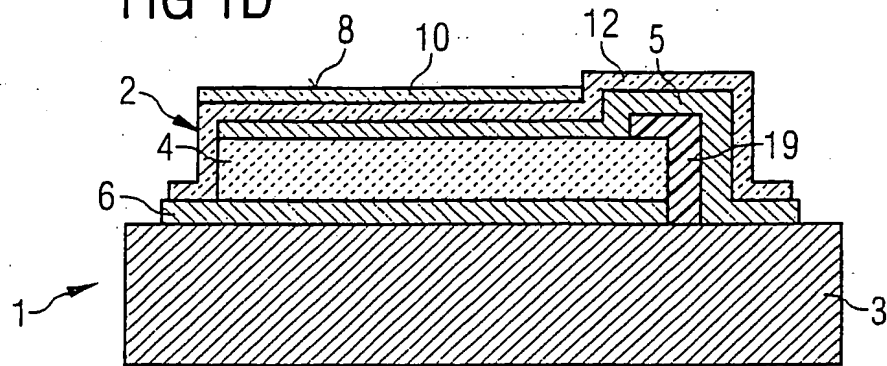


FIG 1E

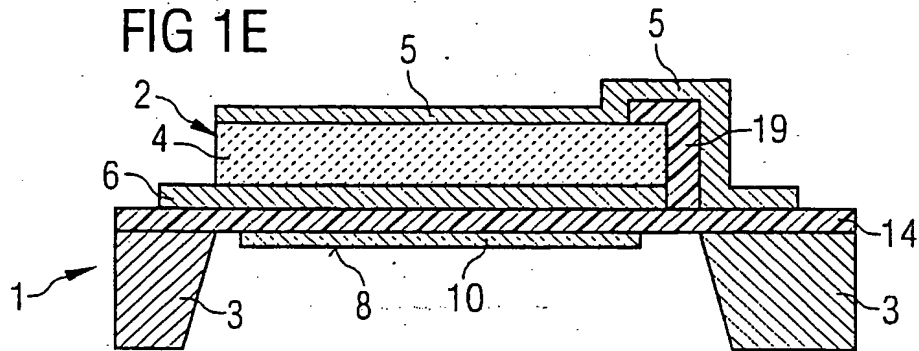
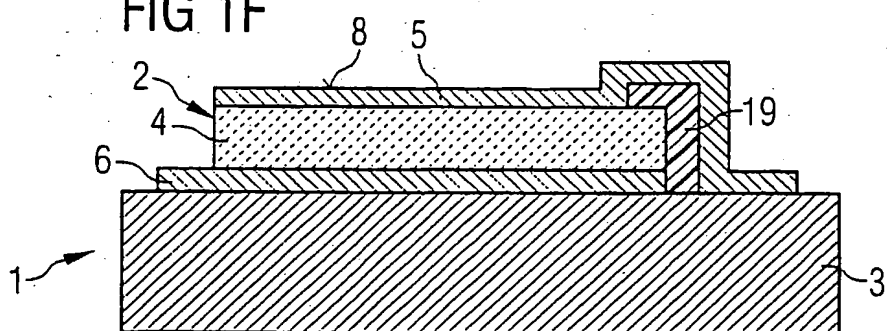


FIG 1F



3/6

FIG 2A

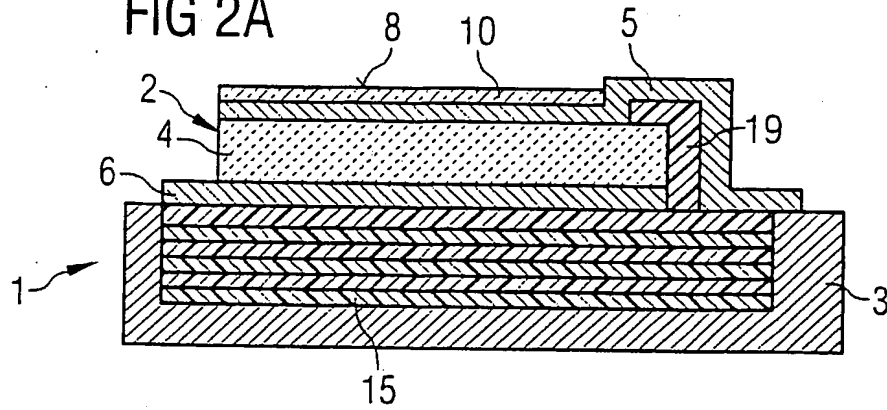


FIG 2B

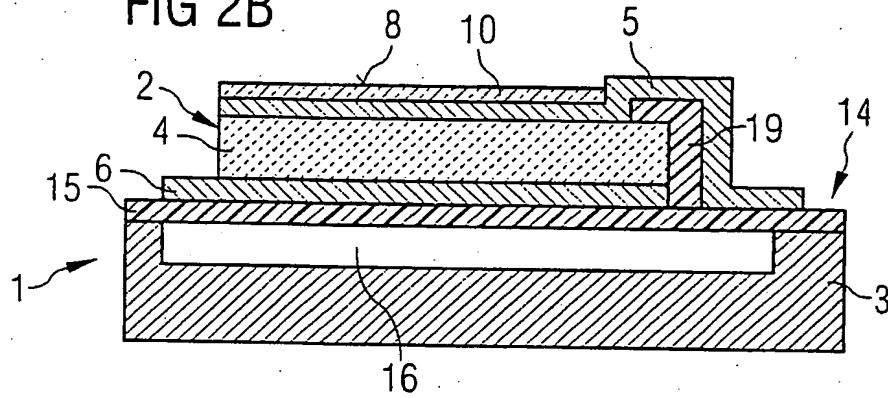
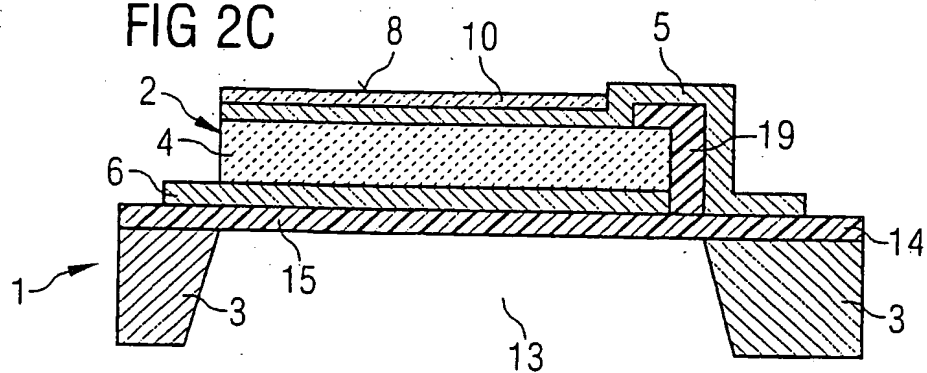


FIG 2C



A detailed cross-sectional diagram of a semiconductor device assembly. The assembly consists of several layers and components. At the top is a thick substrate layer labeled 20. Below it is a thin layer 21, which appears to be a passivation or insulation layer. Underneath 21 are two vertical structures labeled 23, which could be vias or pillars. Between these 23 structures is a central rectangular block labeled 19. To the left of 19 is another rectangular block labeled 4, which sits on a layer labeled 5. A curved arrow labeled 2 points towards the interface between 4 and 5. Below these upper components is a large, complex base structure. This base has a top layer labeled 6, followed by a layer labeled 14. Below 14 is a large block containing internal features labeled 8, 9, 13, 24, and 10. The bottom-most part of the base is a thick layer labeled 25. On the right side of the main assembly, there is a separate rectangular block labeled 18, which is connected to the main structure via a narrow bridge or channel. Various hatching patterns are used throughout the diagram to distinguish different materials or regions.

5/6

FIG 4A

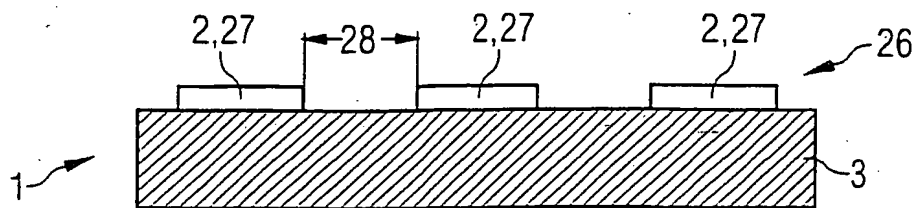


FIG 4B

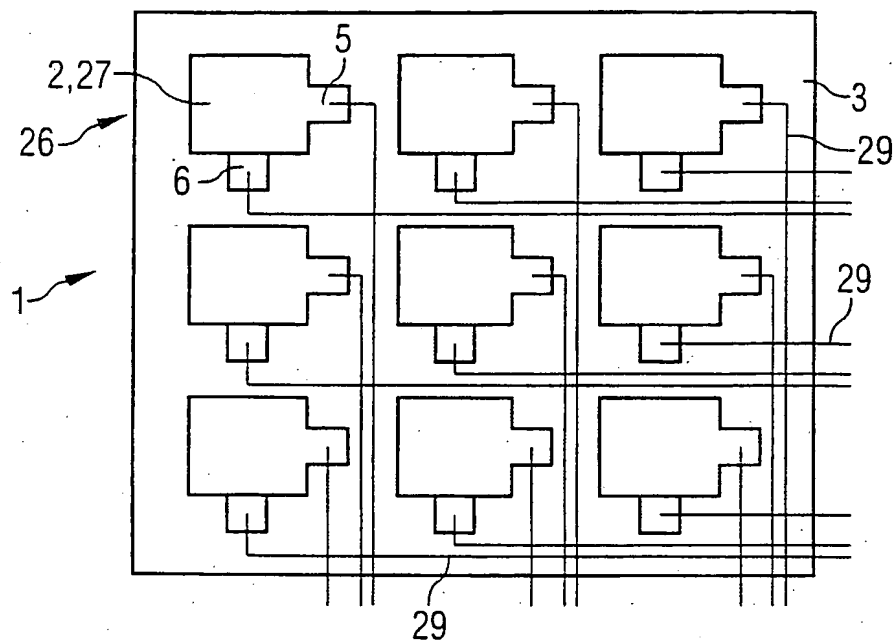
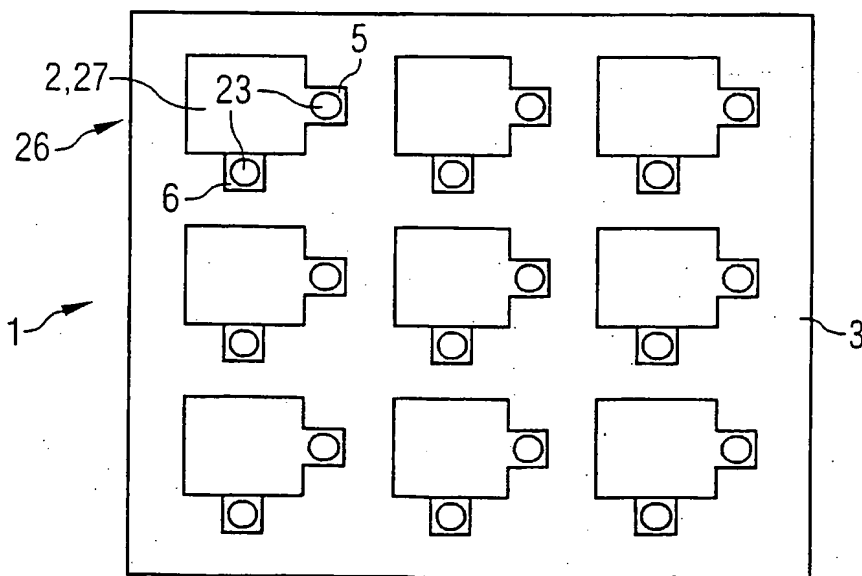


FIG 4C



6/6

FIG 5A

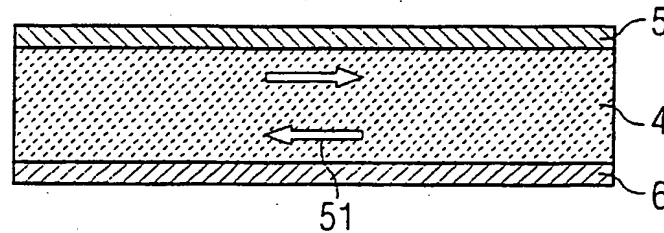


FIG 5B

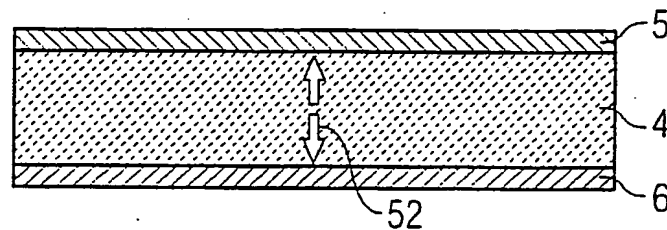


FIG 6

